

IRF7526D1PbF

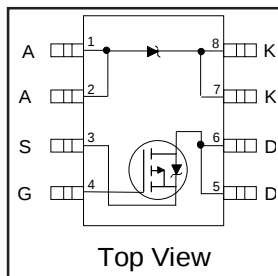
FETKY™ MOSFET & Schottky Diode

- Co-packaged HEXFET® Power MOSFET and Schottky Diode
- P-Channel HEXFET
- Low V_F Schottky Rectifier
- Generation 5 Technology
- Micro8™ Footprint
- Lead-Free

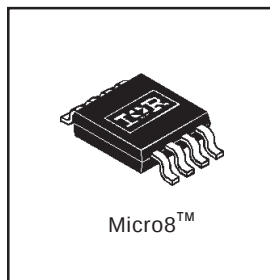
Description

The **FETKY™** family of co-packaged HEXFETs and Schottky diodes offer the designer an innovative board space saving solution for switching regulator applications. Generation 5 HEXFETs utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. Combining this technology with International Rectifier's low forward drop Schottky rectifiers results in an extremely efficient device suitable for use in a wide variety of portable electronics applications like cell phone, PDA, etc.

The new Micro8™ package, with half the footprint area of the standard SO-8, provides the smallest footprint available in an SOIC outline. This makes the Micro8™ an ideal device for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro8™ will allow it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards.



$V_{DSS} = -30V$
$R_{DS(on)} = 0.20\Omega$
Schottky $V_f = 0.39V$



Absolute Maximum Ratings

Parameter	Maximum	Units
I_D @ $T_A = 25^\circ C$	-2.0	A
I_D @ $T_A = 70^\circ C$	-1.6	
I_{DM}	-16	
P_D @ $T_A = 25^\circ C$	1.25	W
P_D @ $T_A = 70^\circ C$	0.8	
	10	mW/°C
V_{GS}	± 20	V
dv/dt	-5.0	V/ns
T_J, T_{STG}	-55 to +150	°C

Thermal Resistance Ratings

Parameter	Maximum	Units
$R_{\theta JA}$	100	°C/W

Notes:

- ① Repetitive rating – pulse width limited by max. junction temperature (see Fig. 9)
- ② $I_{SD} \leq -1.2A$, $di/dt \leq 160A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ C$
- ③ Pulse width $\leq 300\mu s$ – duty cycle $\leq 2\%$
- ④ When mounted on 1 inch square copper board to approximate typical multi-layer PCB thermal resistance

MOSFET Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.17	0.20	Ω	$V_{GS} = -10V, I_D = -1.2A$ ③
		—	0.30	0.40		$V_{GS} = -4.5V, I_D = -0.60A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	—	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	0.94	—	—	S	$V_{DS} = -10V, I_D = -0.60A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	$V_{DS} = -24V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$
Q_g	Total Gate Charge	—	7.5	11	nC	$I_D = -1.2A$
Q_{gs}	Gate-to-Source Charge	—	1.3	1.9		$V_{DS} = -24V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	2.5	3.7		$V_{GS} = -10V$, See Fig. 6 ③
$t_{d(on)}$	Turn-On Delay Time	—	9.7	—	ns	$V_{DD} = -15V$
t_r	Rise Time	—	12	—		$I_D = -1.2A$
$t_{d(off)}$	Turn-Off Delay Time	—	19	—		$R_G = 6.2\Omega$
t_f	Fall Time	—	9.3	—		$R_D = 12\Omega$, ③
C_{iss}	Input Capacitance	—	180	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	87	—		$V_{DS} = -25V$
C_{rss}	Reverse Transfer Capacitance	—	42	—		$f = 1.0\text{MHz}$, See Fig. 5

MOSFET Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-1.25	A	
I_{SM}	Pulsed Source Current (Body Diode)	—	—	-9.6		
V_{SD}	Body Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -1.2A, V_{GS} = 0V$
t_{rr}	Reverse Recovery Time (Body Diode)	—	30	45	ns	$T_J = 25^\circ\text{C}, I_F = -1.2A$
Q_{rr}	Reverse Recovery Charge	—	37	55	nC	$di/dt = 100A/\mu s$ ③

Schottky Diode Maximum Ratings

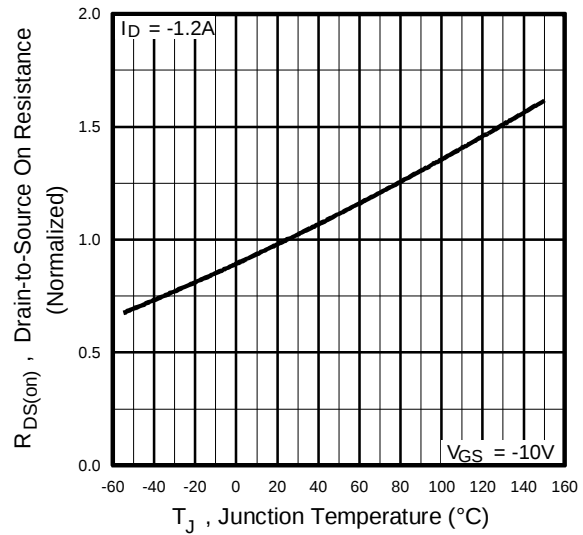
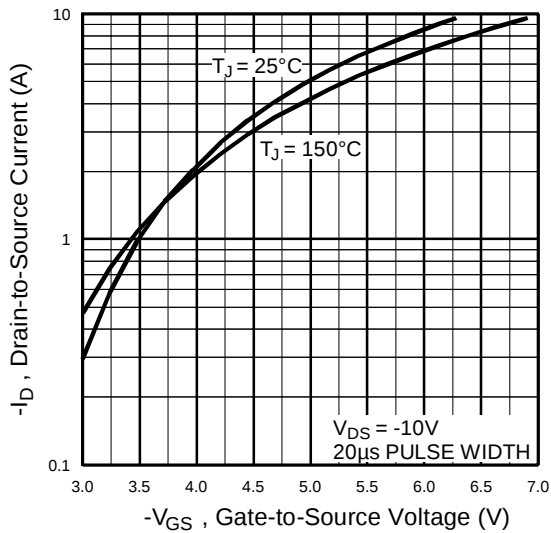
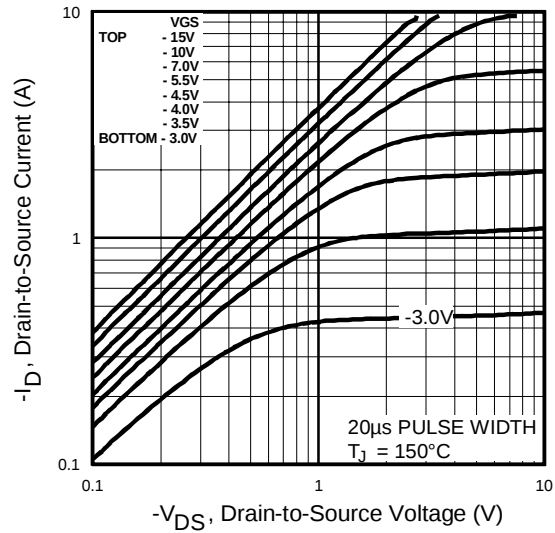
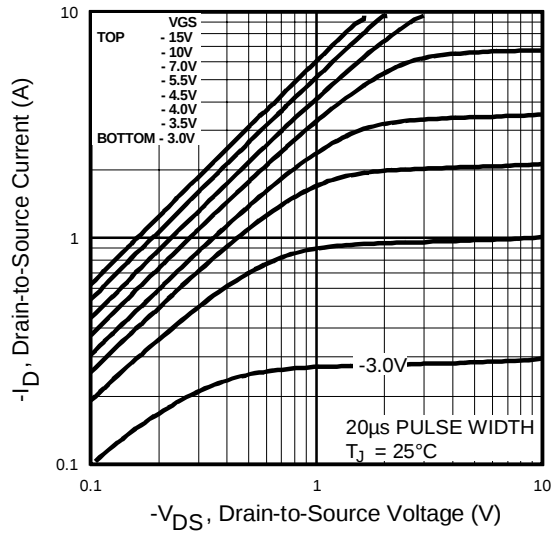
	Parameter	Max.	Units	Conditions
$I_{F(av)}$	Max. Average Forward Current	1.9	A	50% Duty Cycle. Rectangular Wave, $T_A = 25^\circ\text{C}$ See Fig. 14 $T_A = 70^\circ\text{C}$
		1.3		
I_{SM}	Max. peak one cycle Non-repetitive Surge current	120	A	5 μs sine or 3 μs Rect. pulse
		11		10ms sine or 6ms Rect. pulse

Schottky Diode Electrical Specifications

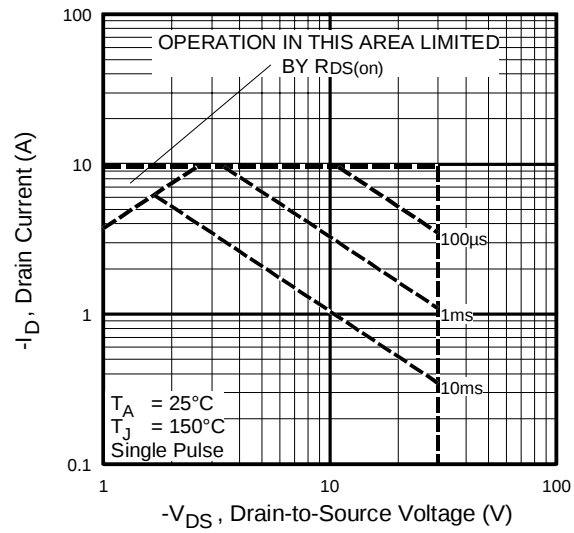
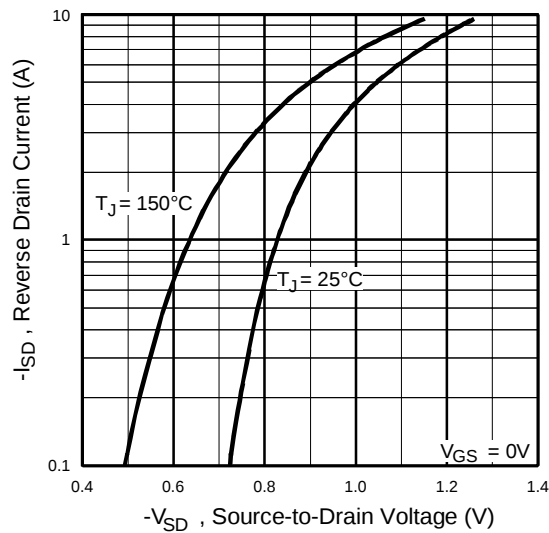
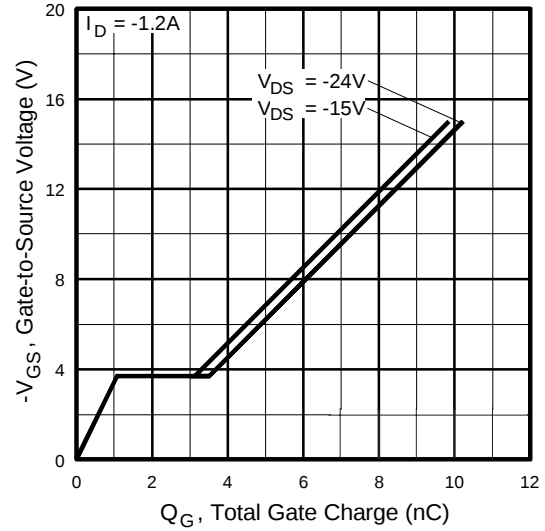
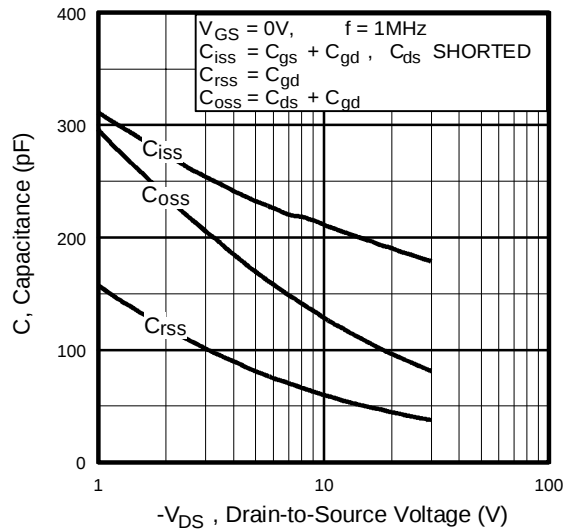
	Parameter	Max.	Units	Conditions
V_{FM}	Max. Forward voltage drop	0.50	V	$I_F = 1.0A, T_J = 25^\circ\text{C}$
		0.62		$I_F = 2.0A, T_J = 25^\circ\text{C}$
		0.39		$I_F = 1.0A, T_J = 125^\circ\text{C}$
		0.57		$I_F = 2.0A, T_J = 125^\circ\text{C}$
I_{RM}	Max. Reverse Leakage current	0.06	mA	$V_R = 30V, T_J = 25^\circ\text{C}$
		16		$T_J = 125^\circ\text{C}$
C_t	Max. Junction Capacitance	92	pF	$V_R = 5Vdc$ (100kHz to 1 MHz) 25°C
dv/dt	Max. Voltage Rate of Charge	3600	V/ μs	Rated V_R

(HEXFET is the reg. TM for International Rectifier Power MOSFET's)

Power Mosfet Characteristics



Power Mosfet Characteristics



Power Mosfet Characteristics

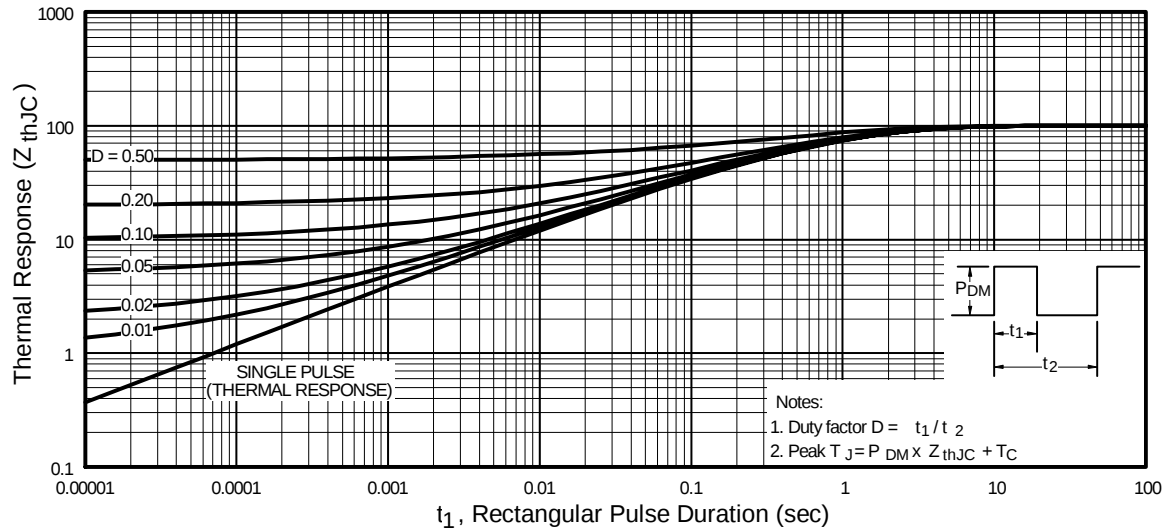


Fig 9. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

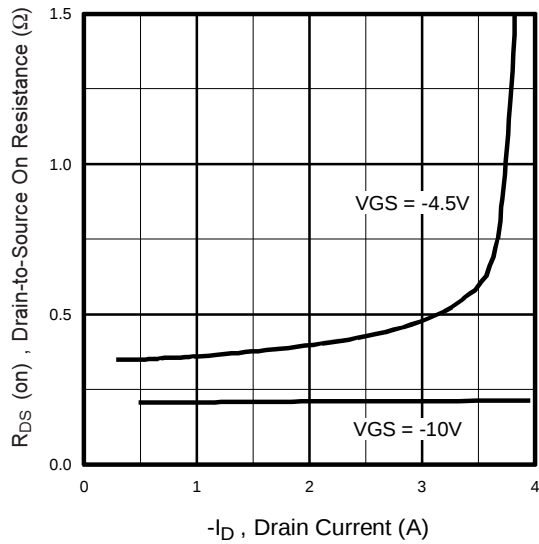


Fig 10. Typical On-Resistance Vs. Drain Current

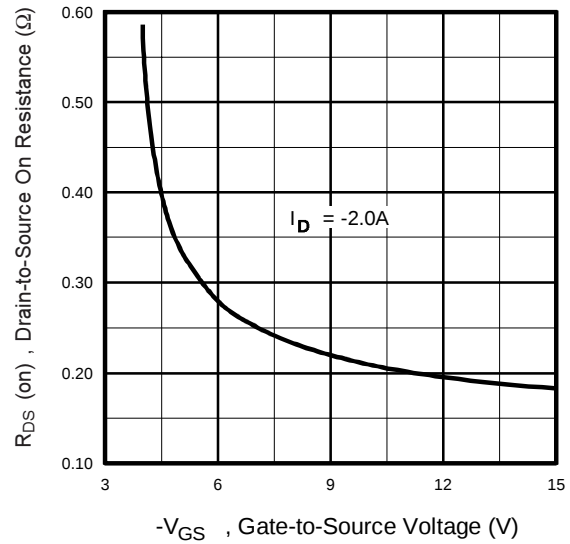


Fig 11. Typical On-Resistance Vs. Gate Voltage

Schottky Diode Characteristics

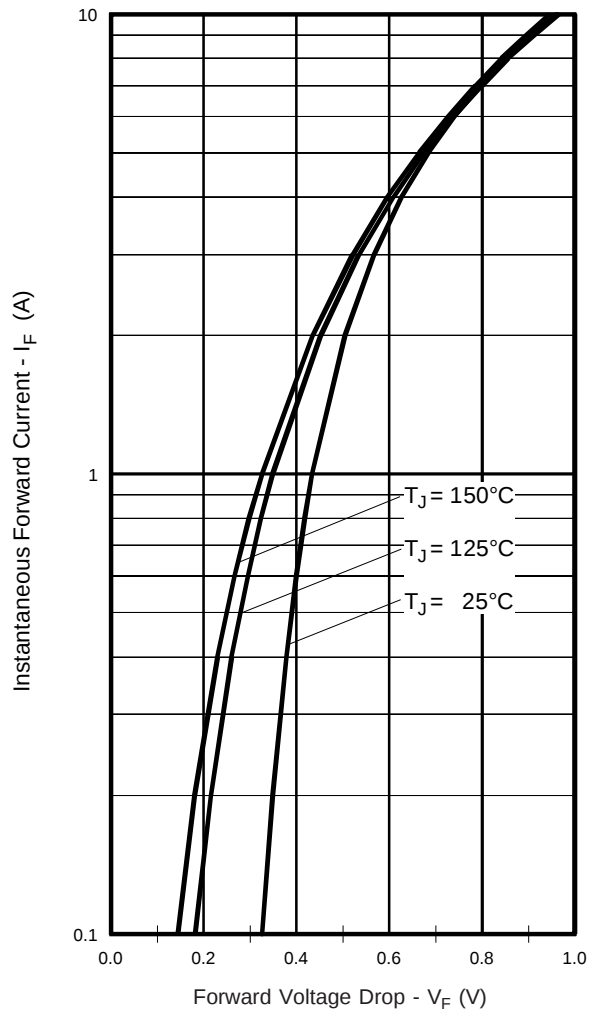


Fig. 12 -Typical Forward Voltage Drop Characteristics

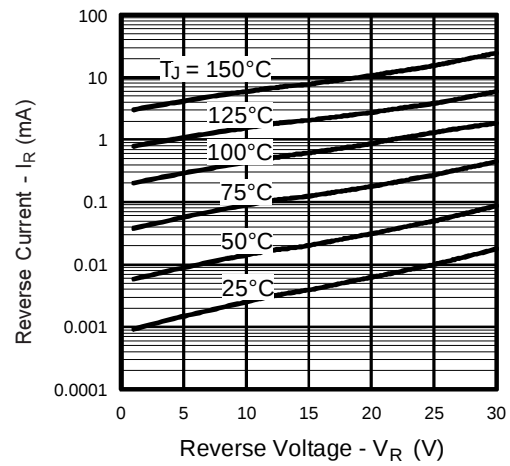


Fig. 13 - Typical Values of Reverse Current Vs. Reverse Voltage

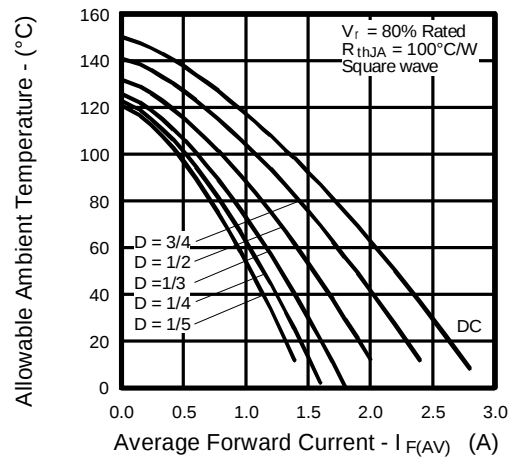


Fig.14 - Maximum Allowable Ambient Temp. Vs. Forward Current

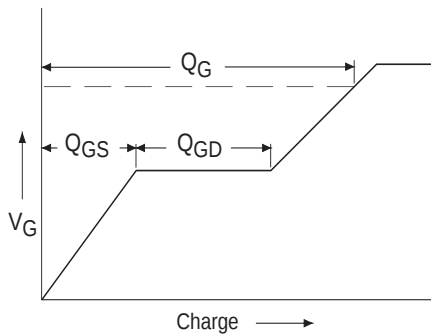


Fig 15a. Basic Gate Charge Waveform

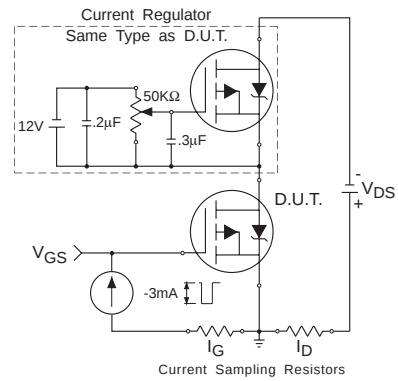


Fig 15b. Gate Charge Test Circuit

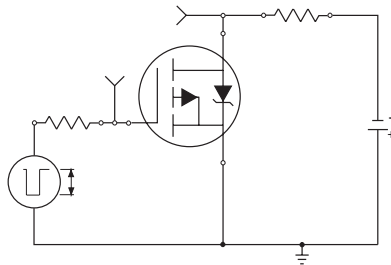


Fig 16a. Switching Time Test Circuit

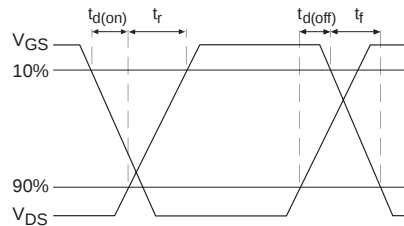
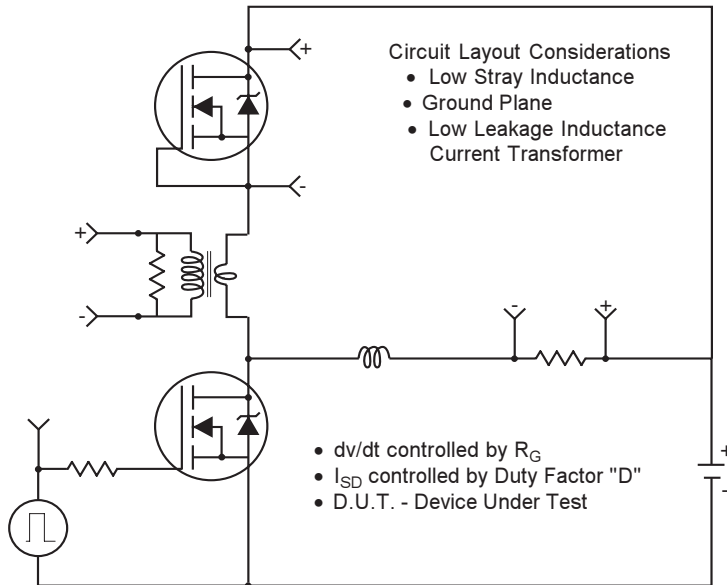


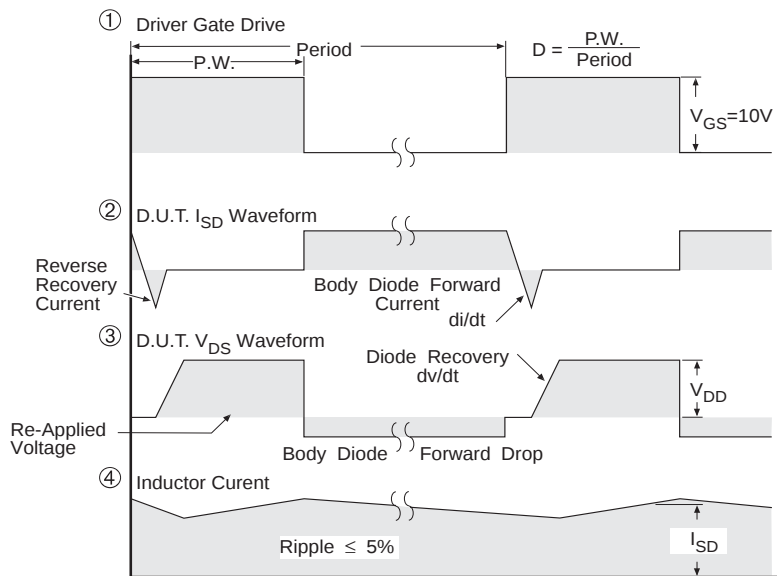
Fig 16b. Switching Time Waveforms

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity for P-Channel

** Use P-Channel Driver for P-Channel Measurements

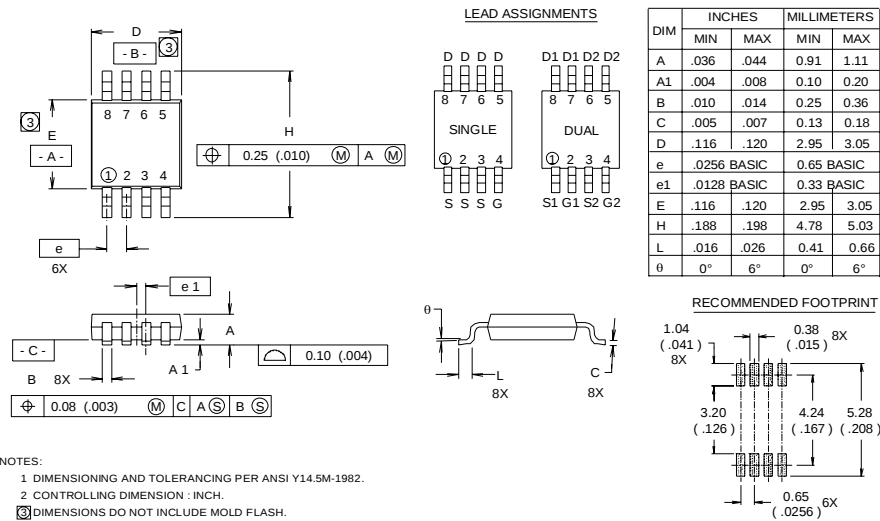


*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

Fig 17 For P Channel HEXFETS

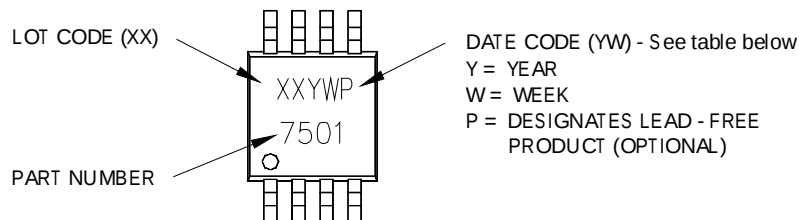
Micro8 Package Outline

Dimensions are shown in millimeters (inches)



Micro8 Part Marking Information

EXAMPLE: THIS IS AN IRF7501



WW = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
2006	6		
2007	7		
2008	8		
2009	9		
2010	0	24	X
		25	Y
		26	Z

WW = (27-52) IF PRECEDED BY A LETTER

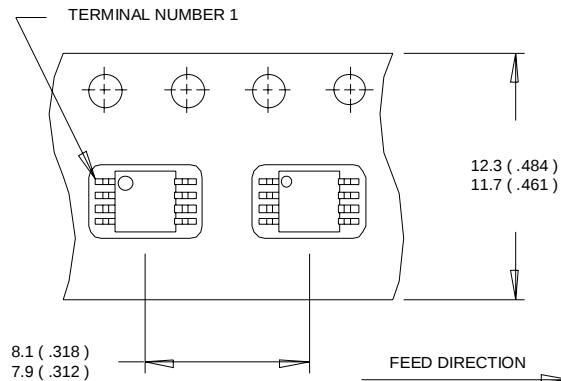
YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
2006	F		
2007	G		
2008	H		
2009	J		
2010	K	50	X
		51	Y
		52	Z

IRF7526D1PbF

International
IR Rectifier

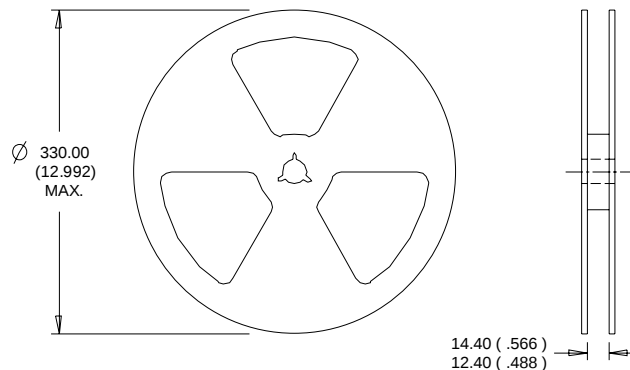
Micro8 Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES:

1. OUTLINE CONFORMS TO EIA-481 & EIA-541.
2. CONTROLLING DIMENSION : MILLIMETER.



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualifications Standards can be found on IR's Web site.

International
IR Rectifier

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